

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics ²⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.6	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=45\text{ }\mu\text{A}$	1.0	1.6	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=30\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.01	1	μA
		$V_{DS}=30\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}^{2)}$	-	10	1000	
		$V_{DS}=18\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=85\text{ °C}^{2)}$	-	5	60	
Gate-source leakage current	I_{GSS}	$V_{GS}=16\text{ V}$, $V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}$, $I_D=40\text{ A}$	-	3.9	5	m Ω
		$V_{GS}=4.5\text{ V}$, $I_D=40\text{ A}$, SMD version	-	3.6	4.7	
		$V_{GS}=10\text{ V}$, $I_D=80\text{ A}$	-	3.0	3.7	
		$V_{GS}=10\text{ V}$, $I_D=80\text{ A}$, SMD version	-	2.7	3.4	

Parameter	Symbol	Conditions	Values			Unit
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Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	4000	5100	pF
Output capacitance	C_{oss}		-	1000	1300	
Reverse transfer capacitance	C_{rss}		-	53	100	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$ $I_D=80\text{ A}, R_G=3.5\ \Omega$	-	9	-	ns
Rise time	t_r		-	6	-	
Turn-off delay time	$t_{d(off)}$		-	37	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=24\text{ V}, I_D=80\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	12	15	nC
Gate to drain charge	Q_{gd}		-	8	16	
Gate charge total	Q_g		-	60	75	
Gate plateau voltage	$V_{plateau}$		-	3.1	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25\text{ °C}$	-	-	80	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	320	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=80\text{ A},$ $T_J=25\text{ °C}$	0.6	0.9	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=15\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	60	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	50	-	

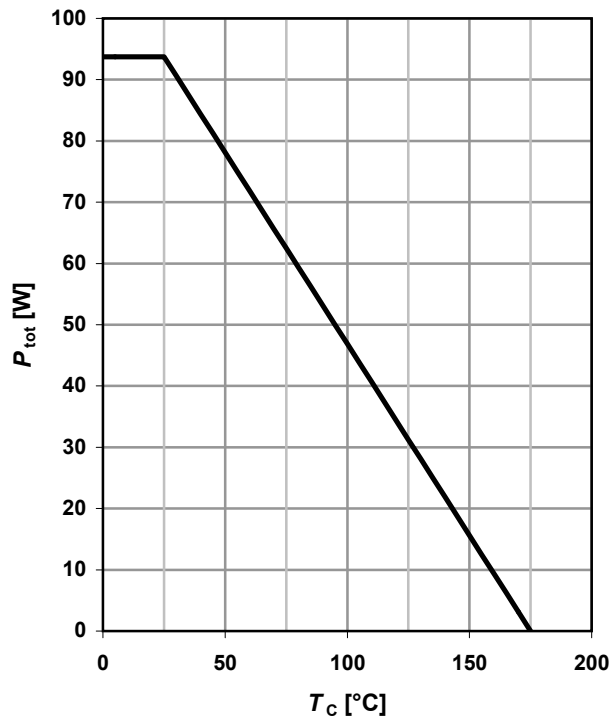
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 1.6\text{K/W}$ the chip is able to carry 128A at 25°C.

²⁾ Defined by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

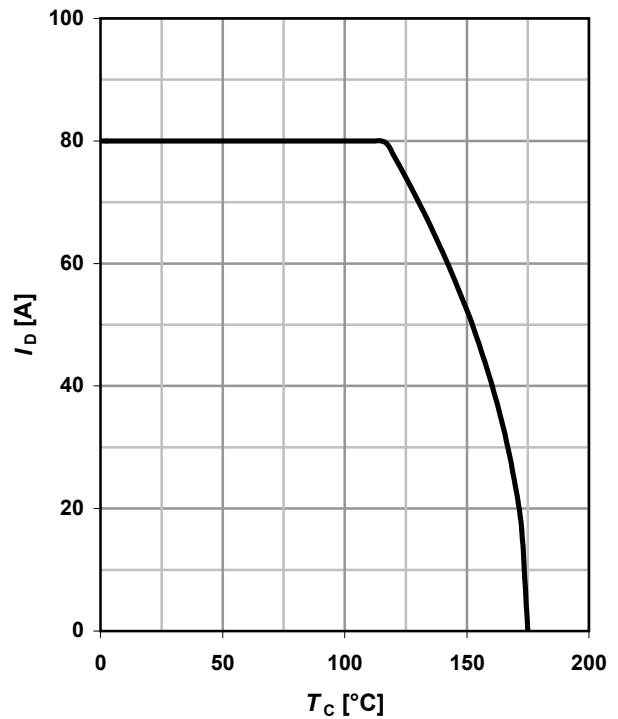
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



2 Drain current

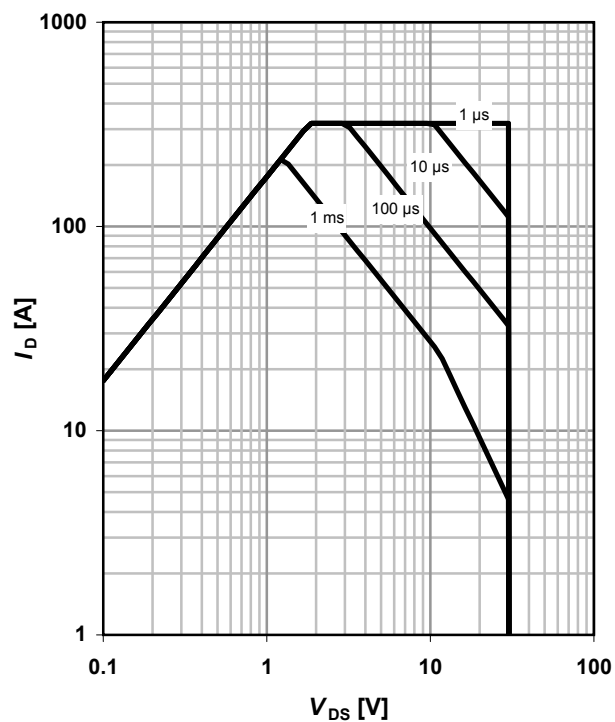
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}; \text{SMD}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0, \text{SMD}$$

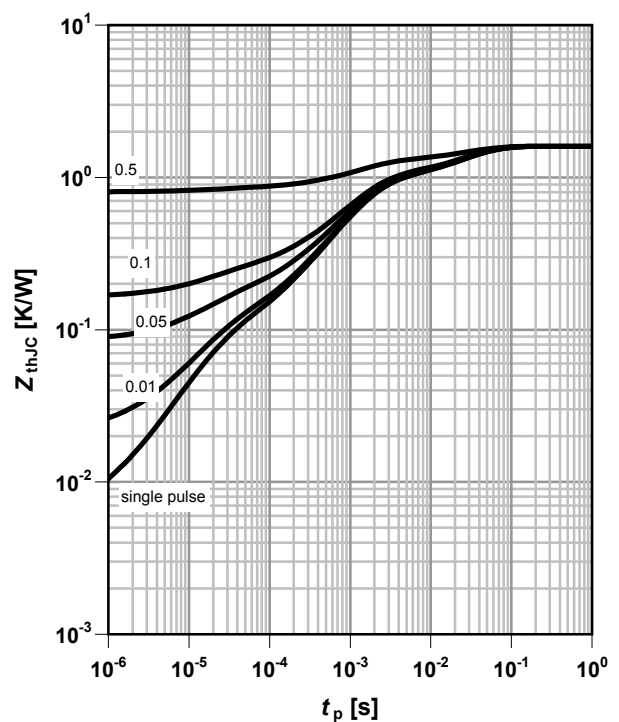
parameter: t_p



4 Max. transient thermal impedance

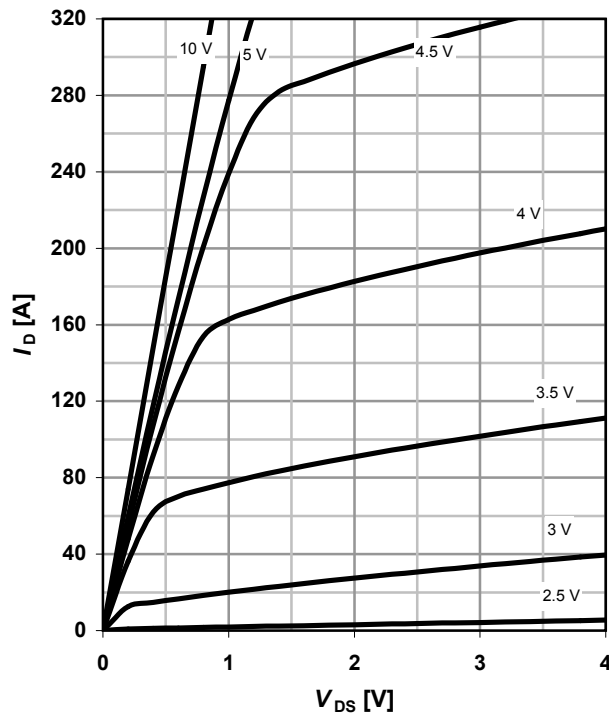
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$



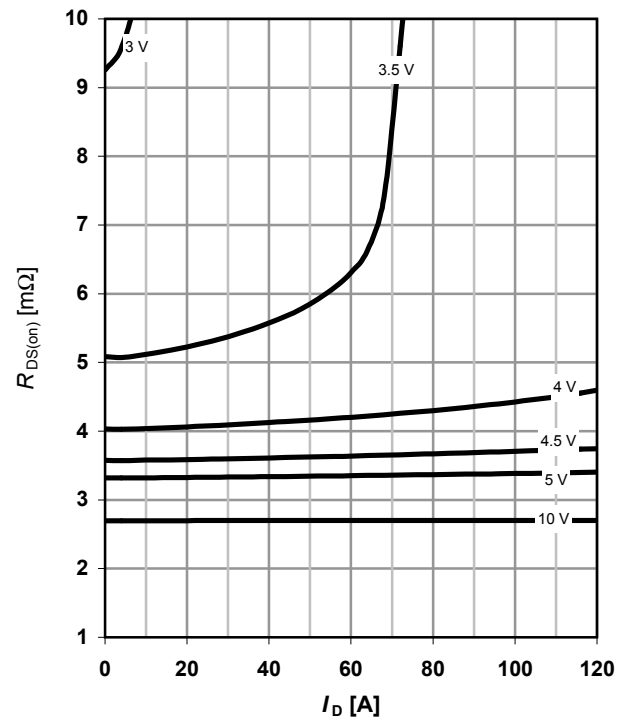
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}, \text{SMD}$

parameter: V_{GS}


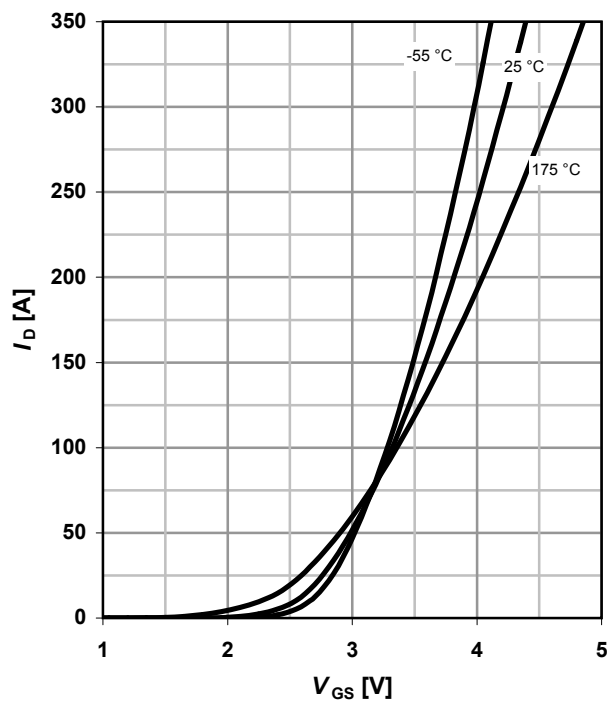
6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}, \text{SMD}$

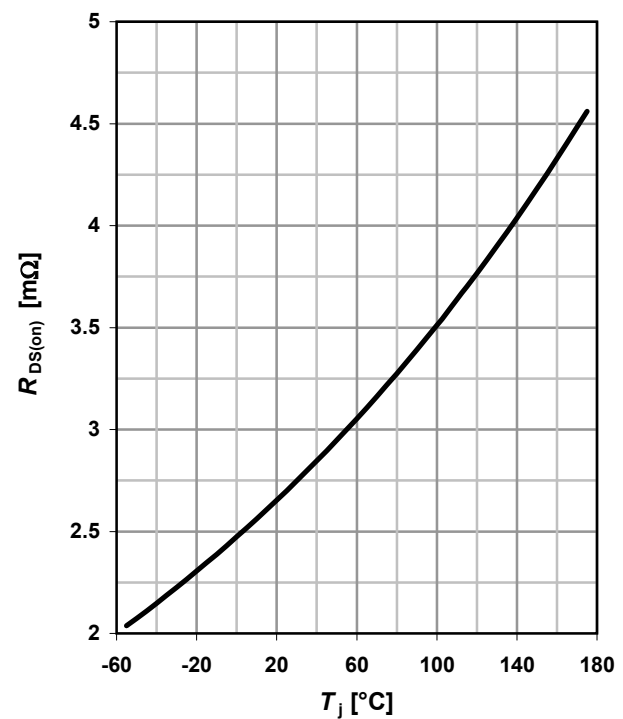
parameter: V_{GS}


7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{V}$

parameter: T_j


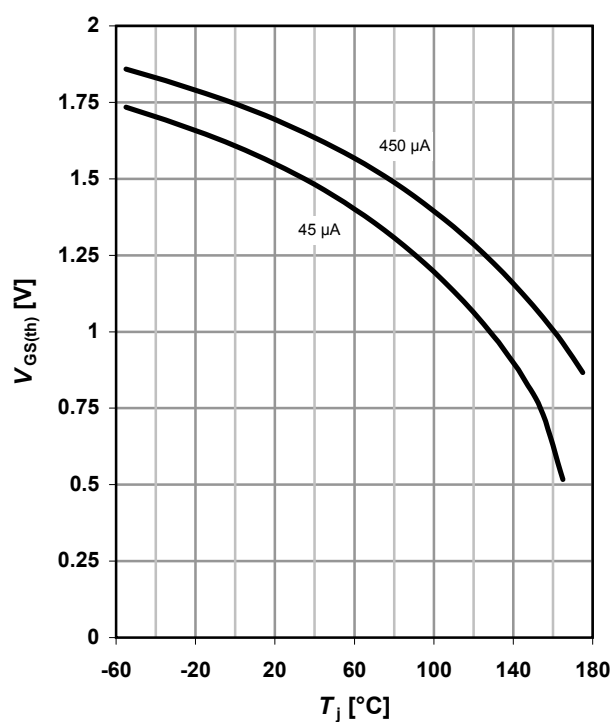
8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 80\text{ A}; V_{GS} = 10\text{ V}, \text{SMD}$


9 Typ. gate threshold voltage

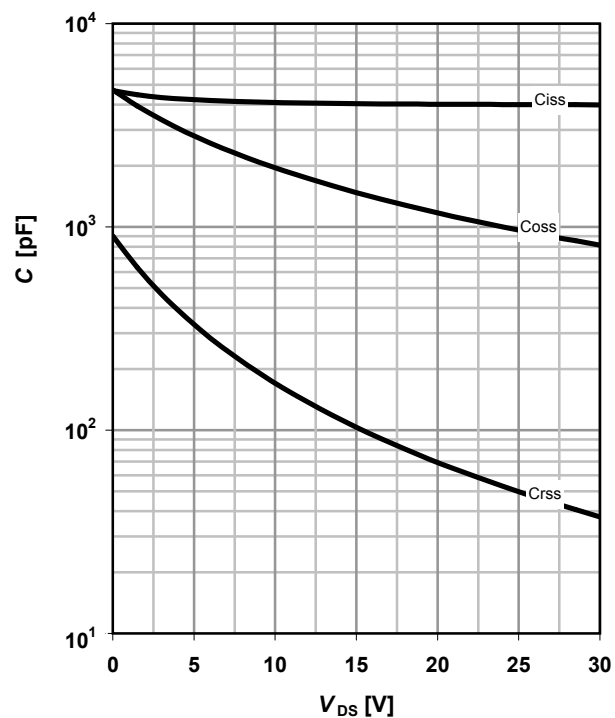
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 Typ. capacitances

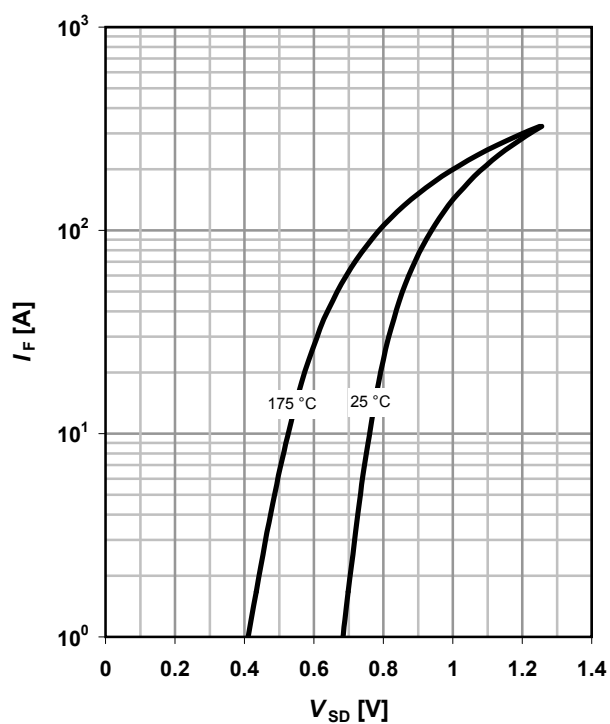
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$



11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

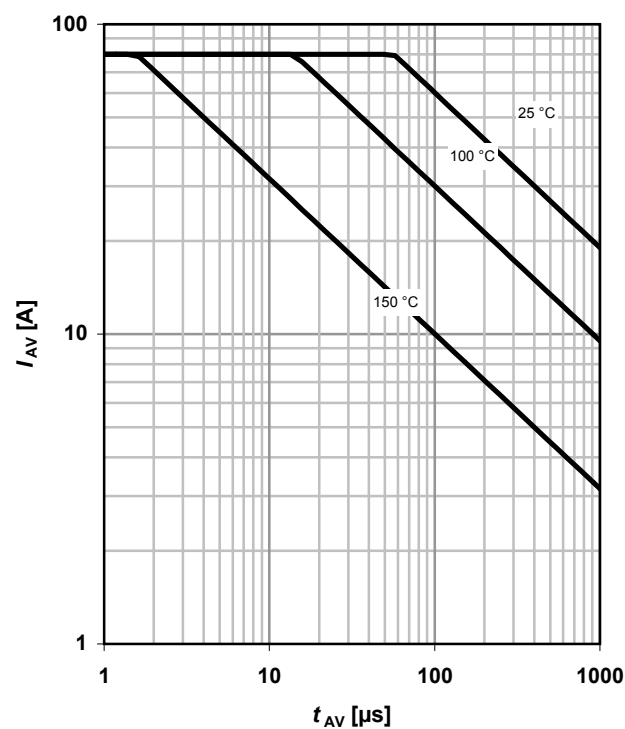
parameter: T_j



12 Typ. avalanche characteristics

$$I_{AS} = f(t_{AV})$$

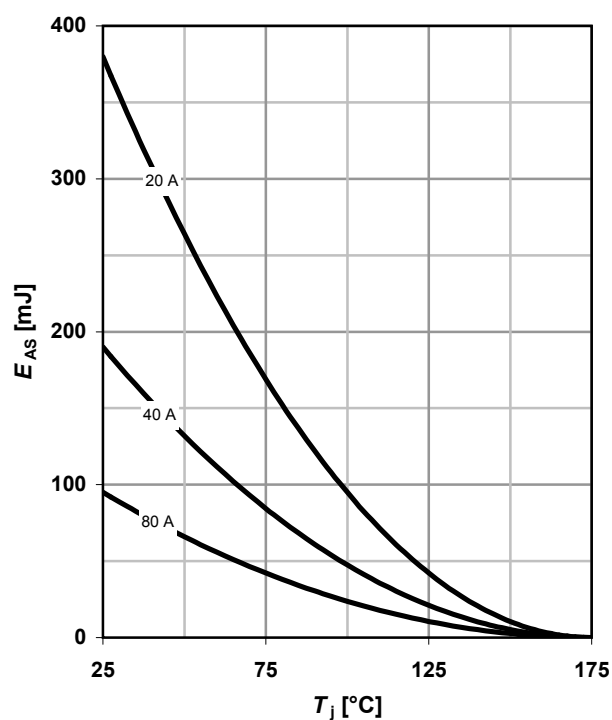
parameter: $T_{j(start)}$



13 Typical avalanche energy

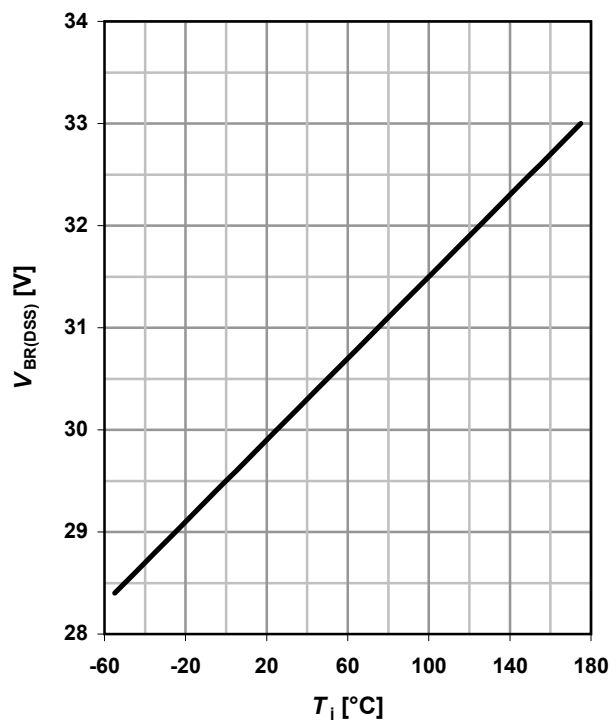
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Typ. drain-source breakdown voltage

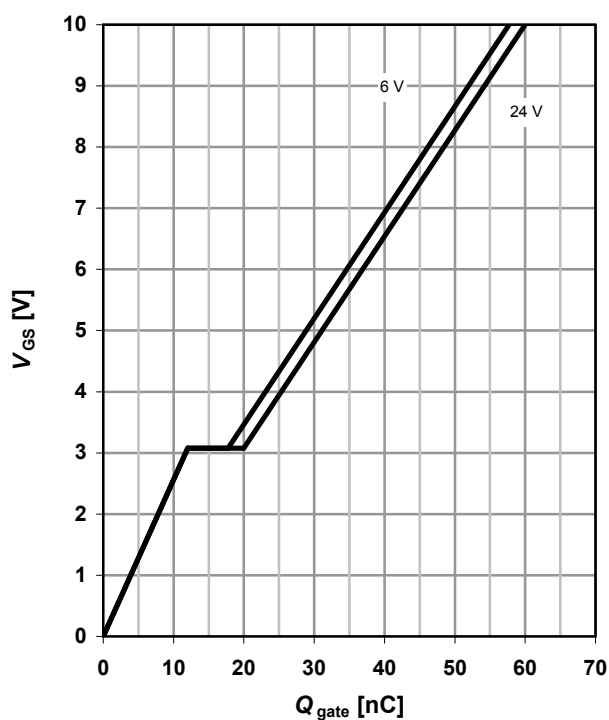
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



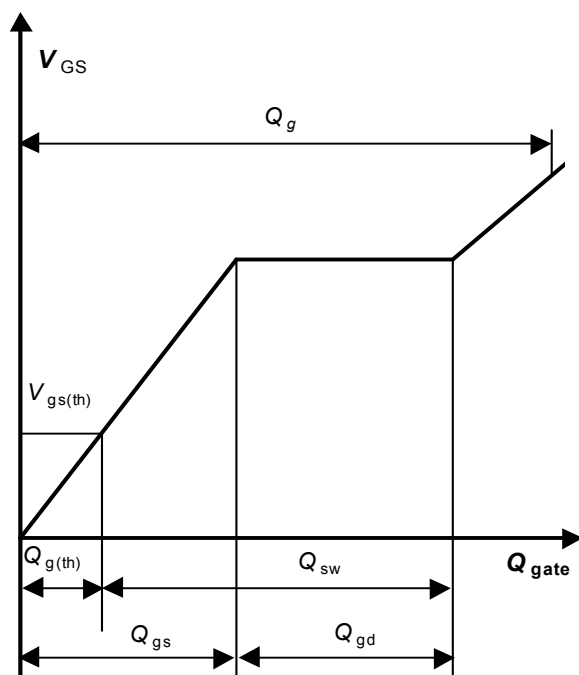
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 80 \text{ A pulsed}$$

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

Version	Date	Changes
Rev 2.0	09.03.2007	Final data sheet
Rev 2.1	08.03.2010	Update of RDSon